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FDS8433A

Single P-Channel 2.5V Specified MOSFET

General Description

This P-Channel enhancement mode power field effect transistors is produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density processis especially tailored to minimize on-state resistance and provide superior switching performance.

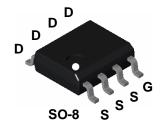
Applications

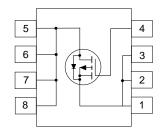
- Load switch
- DC/DC converter
- Battery protection

Features

• -5 A, -20 V. R
$$_{DS(on)}$$
 = 0.047 Ω @ V $_{GS}$ = -4.5 V $_{DS(on)}$ = 0.070 Ω @ V $_{GS}$ = -2.5 V

- Fast switching speed.
- High density cell design for extremely low R_{DS(on)}.
- High power and current handling capability.





Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		FDS8433A	Units
V _{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage		<u>+</u> 8	V
I _D	Drain Current - Continuous	(Note 1a)	-5	Α
	- Pulsed		-50	
P _D	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1	
T _J , T _{stg}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta^{JA}}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	∘C/W
$R_{\theta^{JC}}$	Thermal Resistance, Junction-to-Case	(Note 1)	25	∘C/W

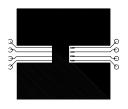
Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDS8433A	FDS8433A	13"	12mm	2500 units

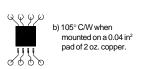
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-20			V
BVpss ΔΤ,	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-25		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 8 V, V _{DS} = 0 V			100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -8 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-0.4	-0.6	-1	V
$\Delta V_{GS(th)} = \Delta T_{J}$	Gate Threshold Voltage Temperature Coefficient	I_D = -250 μA, Referenced to 25°C		4		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = -4.5 \text{ V}, I_D = -5 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -5 \text{ A}, T_J = 125^{\circ}\text{C}$		0.036 0.050	0.047 0.085	Ω Ω
		$V_{GS} = -2.5 \text{ V}, I_D = -4.3 \text{ A}$		0.047	0.070	Ω
I _{D(on)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$	-25			A
g _{FS}	Forward Transconductance	$V_{DS} = -5 \text{ V}, I_{D} = -5 \text{ A}$		16		S
<u>Dynamic</u>	Characteristics	<u>, </u>		ı	ı	
C _{iss}	Input Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$		1130		pF
Coss	Output Capacitance	f = 1.0 MHz		480		pF
C _{rss}	Reverse Transfer Capacitance			120		pF
Switchin	ng Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -10 \text{ V}, I_{D} = -1 \text{ A},$		8	16	ns
t _r	Turn-On Rise Time	V_{GS} = -4.5 V, R_{GEN} = 6 Ω		23	37	ns
t _{d(off)}	Turn-Off Delay Time			260	360	ns
t _f	Turn-Off Fall Time			90	125	ns
Q _g	Total Gate Charge	$V_{DS} = -5 \text{ V}, I_{D} = -5 \text{ A},$		20	28	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -5 V$,		2.8		nC
Q_{gd}	Gate-Drain Charge			3.2		nC
Drain-Sc	ource Diode Characteristics an	d Maximum Ratings				
I _s	Maximum Continuous Drain-Source Did				-2.1	А

Notes:

^{1:} R_{BJA} is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50° C/W when mounted on a 1 in² pad of 2 oz. copper.



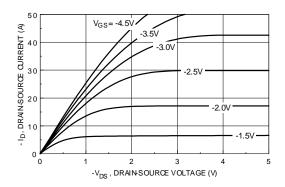


c) 125° C/W on a minimum mounting pad of 2 oz. copper.

Scale 1: 1 on letter size paper

2: Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Typical Characteristics



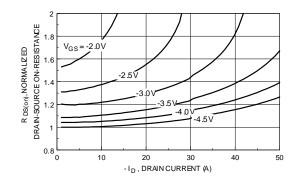
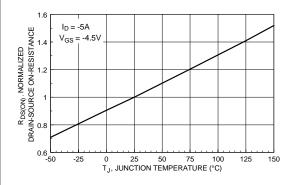


Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.



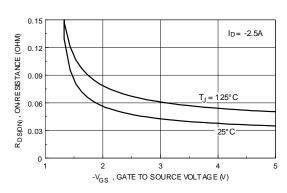
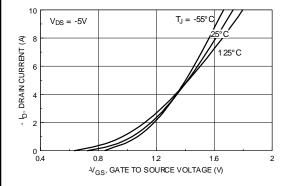


Figure 3. On-Resistance Variation with Temperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



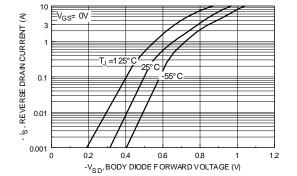
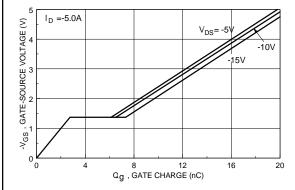


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)



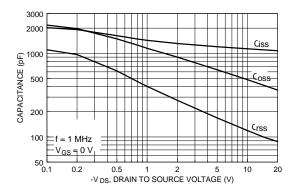
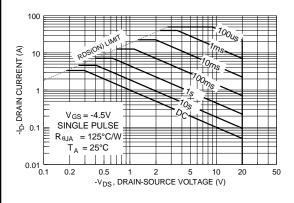


Figure 7. Gate-Charge Characteristics.





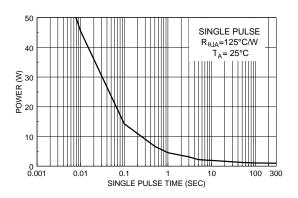


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

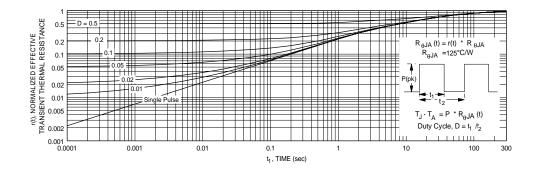


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1. Transient themal response will change depending on the circuit board design.

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